

Loadless 4T SRAM cell with PMOS drivers

ABSTRACT

5 The instant invention comprises a memory cell with PMOS drive
transistors (170, 180) and NMOS pass transistors (150, 160). A
NMOS transistor is connected between a storage node (230) and a
bitline (200). The NMOS transistor is gated by the wordline
(190). A PMOS drive transistor (180) is connected between the
10 storage node (230) and a supply voltage (255).